



JCT640CH 40A SCR

Rev.A.1.1

DESCRIPTION:

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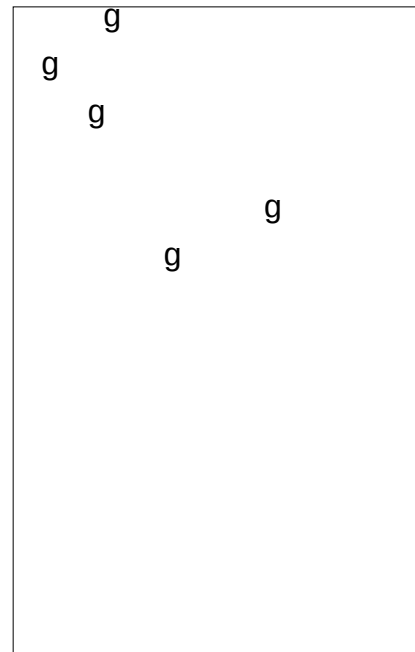
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MAIN FEATURES

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage temperature	T_s	-40-150	°C
Operating junction temperature	T_j	-40-150	°C
Reverse blocking voltage (T _j =25 °C)	V_{DRM}	600	V
Reverse peak voltage (T _j =25 °C)	V_{RRM}	600	V
Average current (T _a =134 °C)	$I_{T(AV)}$	25	A
RMS on-state current (T _a =134 °C)	$I_{T(RMS)}$	40	A
Non-repetitive peak current (t _p =10ms, T _j =25 °C)	I_{TSM}	500	A
Non-repetitive peak current (t _p =8.3ms, T _j =25 °C)		540	
Surge current (t _p =10ms, T _j =25 °C)	I^2t	1250	A ² s
Gate trigger voltage (I _G =2× I _{GT} , f=100Hz)	di/dt	180	A/μs
Peak gate current (t _p =20μs, T _j =150 °C)	I_{GM}	10	A
Average power dissipation (T _j =150 °C)	$P_{G(AV)}$	1	W

ORDERING INFORMATION

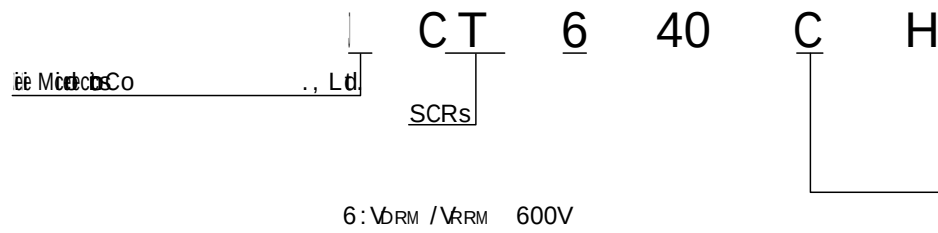


FIG.1: M_{DSS}
RMS σ - δ σ

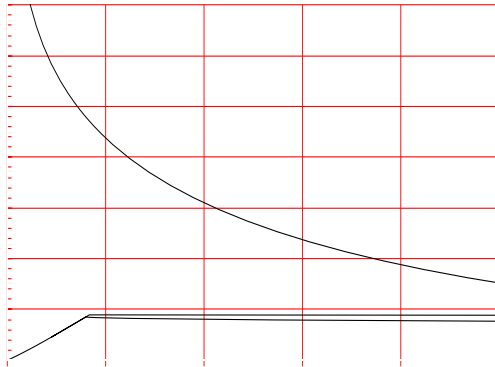


FIG.2: RMS σ - δ σ
 σ

